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September 2014

### FDMA86151L

# Single N-Channel PowerTrench® MOSFET

**100 V, 3.3 A, 88 m**Ω

#### **Features**

- Max  $r_{DS(on)}$  = 88 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 3.3 A
- Max  $r_{DS(on)}$  = 132 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 2.7 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

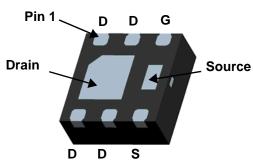
### **General Description**

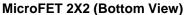
This device has been designed to provide maximum efficiency and thermal performance for synchronous buck converters. The low rDS(on) and gate charge provide excellent switching performance.

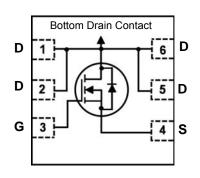
### **Application**

■ DC – DC Buck Converters









### MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Paran		Ratings	Units	
$V_{DS}$	Drain to Source Voltage			100	V
$V_{GS}$	Gate to Source Voltage			±20	V
1	Drain Curre -Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	3.3	^
ID	-Pulsed		(Note 3)	20	A
D	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.4	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1b)	0.9	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temper	rature Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
151	FDMA86151L	MicroFET 2X2	7 "	8 mm	3000 units

### Electrical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		69		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA

#### **On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		-6		mV/°C
	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.3 A		60	88	
r		$V_{GS} = 4.5 \text{ V}, I_D = 2.7 \text{ A}$		83	132	mΩ
r <sub>DS(on)</sub> Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.3 A, T <sub>J</sub> = 125 °C		102	150	11132	
g <sub>FS</sub>	Forward Transconductance	V <sub>DD</sub> = 5 V, I <sub>D</sub> = 3.3 A		8.6		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance			322	450	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$		55	80	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 101112		3	5	pF
$R_{g}$	Gate Resistance		0.1	1.9	3.8	Ω

### **Switching Characteristics**

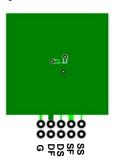
t <sub>d(on)</sub>	Turn-On Delay Time			5.6	12	ns
t <sub>r</sub>	Rise Time	$V_{DD}$ = 50V, $I_{D}$ = 3.3 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		1.4	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω		11	20	ns
t <sub>f</sub>	Fall Time			1.6	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V		5.2	7.3	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 50 \text{ V}$		2.6	3.7	nC
$Q_{gs}$	Gate to Source Charge	I <sub>D</sub> = 3.3 A		1.1		nC
$Q_{ad}$	Gate to Drain "Miller" Charge			1.0		nC

#### **Drain-Source Diode Characteristics**

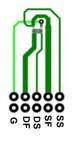
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 3.3 \text{ A}$ (Note 2)		0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>E</sub> = 3.3 A. di/dt = 100 A/us		33	53	ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 3.3 A, αl/αt = 100 A/μs		25	40	nC

#### NOTES

<sup>1.</sup>  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



 a. 52 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



 b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300  $\mu\text{s},$  Duty cycle < 2.0%.
- 3. Pulsed Id limited by junction temperature, td<=10  $\mu$ S, please refer to SOA curve for more details.

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

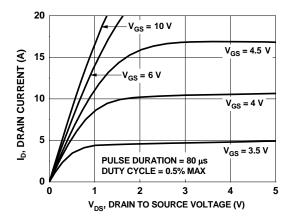


Figure 1. On-Region Characteristics

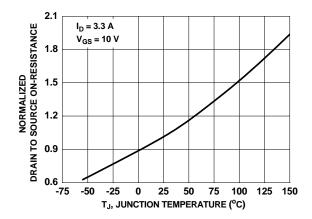


Figure 3. Normalized On-Resistance vs Junction Temperature

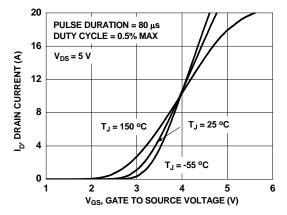


Figure 5. Transfer Characteristics

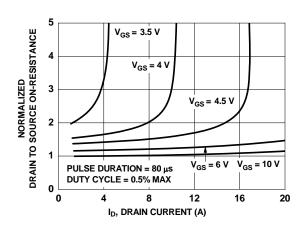


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

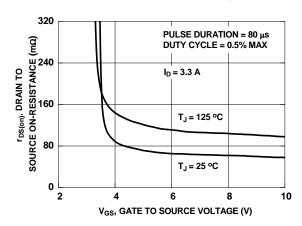


Figure 4. On-Resistance vs Gate to Source Voltage

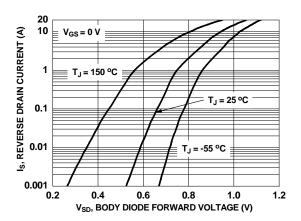


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### **Typical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

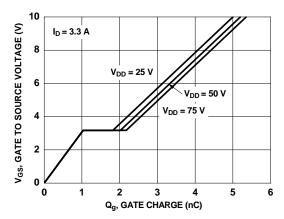


Figure 7. Gate Charge Characteristics

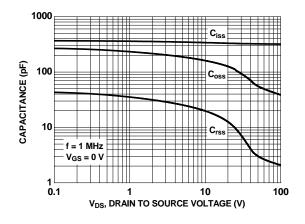


Figure 8. Capacitance vs Drain to Source Voltage

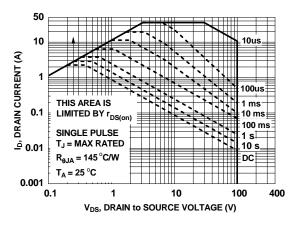


Figure 9. Forward Bias Safe Operating Area

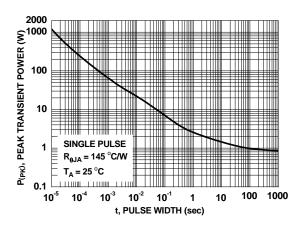


Figure 10. Single Pulse Maximum Power Dissipation

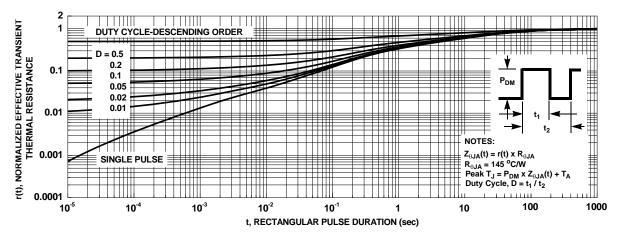
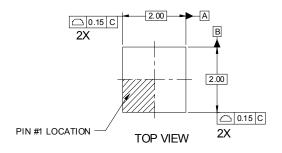
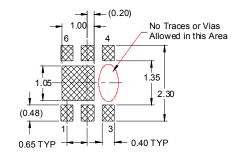


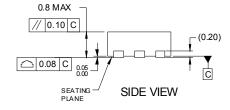
Figure 11. Single Pulse Junction-to-Ambient Transient Thermal Response Curve

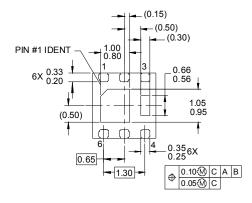
### **Dimensional Outline and Pad Layout**

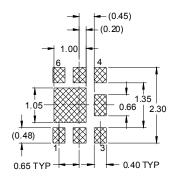




RECOMMENDED LAND PATTERN OPT 1







**BOTTOM VIEW** 

RECOMMENDED LAND PATTERN OPT 2

#### NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003
- B. DIMENSIONS ARE IN MILLIMETERS.
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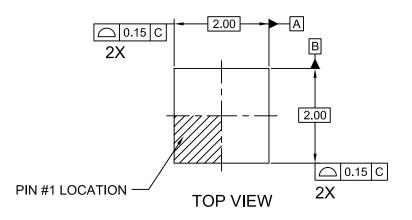
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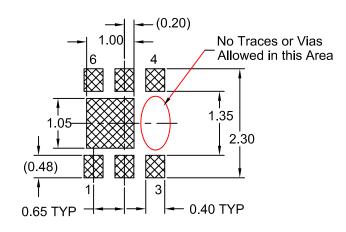
#### PRODUCT STATUS DEFINITIONS

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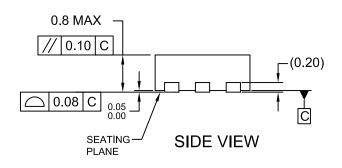
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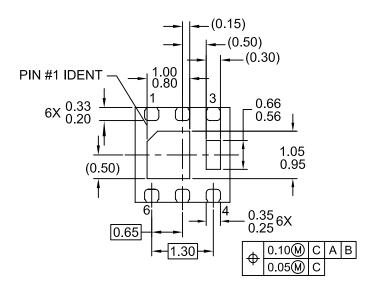
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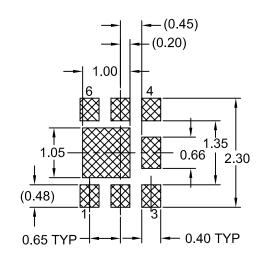




### **RECOMMENDED LAND PATTERN OPT 1**







RECOMMENDED LAND PATTERN OPT 2

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